

Fei Ding

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	FinFET Evolution Toward Stacked-Nanowire FET for CMOS Technology Scaling. IEEE Transactions on Electron Devices, 2015, 62, 3945-3950.	3.0	46
2	Simulation-Based Study of the Inserted-Oxide FinFET for Future Low-Power System-on-Chip Applications. IEEE Electron Device Letters, 2015, 36, 742-744.	3.9	25
3	Simulation-Based Study of Hybrid Fin/Planar LDMOS Design for FinFET-Based System-on-Chip Technology. IEEE Transactions on Electron Devices, 2017, 64, 4193-4199.	3.0	25
4	Sub-lithographic Patterning via Tilted Ion Implantation for Scaling Beyond the 7-nm Technology Node. IEEE Transactions on Electron Devices, 2017, 64, 231-236.	3.0	6
5	Simulation-Based Study of Si/Si _{0.9} Ge _{0.1} /Si Hetero-Channel FinFET for Enhanced Performance in Low-Power Applications. IEEE Electron Device Letters, 2019, 40, 363-366.	3.9	4
6	Novel Doping Engineering Techniques for Gallium Oxide MOSFET to Achieve High Drive Current and Breakdown Voltage. , 2019, , .		4
7	Cell Ratio Tuning for High-Density SRAM Voltage Scaling With Inserted-Oxide FinFETs. IEEE Electron Device Letters, 2016, 37, 1539-1542.	3.9	3
8	Simulation-Based Study of High-Density SRAM Voltage Scaling Enabled by Inserted-Oxide FinFET Technology. IEEE Transactions on Electron Devices, 2019, 66, 1754-1759.	3.0	3
9	Simulation-Based Study of Low Minimum Operating Voltage SRAM With Inserted-Oxide FinFETs and Gate-All-Around Transistors. IEEE Transactions on Electron Devices, 2022, 69, 1823-1829.	3.0	3